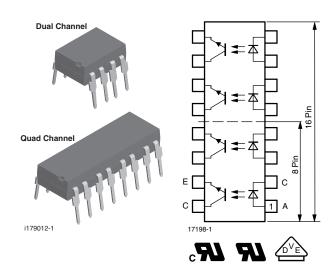


Vishay Semiconductors

### **Optocoupler, Phototransistor Output, (Dual, Quad Channel)**



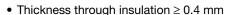
#### **DESCRIPTION**

The TCET2100/TCET4100 consists of a phototransistor optically coupled to a gallium arsenide infrared-emitting diode, available in 8 pin (dual channel) and 16 pin (quad channel) package.

#### **FEATURES**

- Extra low coupling capacity typical 0.2 pF
- High common mode rejection
- Low temperature coefficient of CTR
- Rated impulse voltage (transient overvoltage)
   V<sub>IOTM</sub> = 10 kV peak





 Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC

#### **AGENCY APPROVALS**

- UL1577, file no. E52744 system code H, double protection
- CSA 22.2 bulletin 5A, double protection
- DIN EN 60747-5-5 (VDE 0884)
- FIMKO

ORDE	ORDERING INFORMATION										
[1	г	С	E	Т	#	1	0	0	DIP		
				PART N	UMBER				7.62 mm		
AGENC	Y CER	TIFIED/PAC	KAGE				CTR (%	)			
UL, cUL, VDE							50 to 60	0			
DIP-8, d	DIP-8, dual channel			TCET2100							
DIP-16, quad channel				•			TCET410	0			

### TCET2100, TCET4100



## Vishay Semiconductors Optocoupler, Phototransistor Output, (Dual, Quad Channel)

<b>ABSOLUTE MAXIMUM RATINGS</b> (1) (T <sub>amb</sub> = 25 °C, unless otherwise specified)								
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT				
INPUT								
Reverse voltage		$V_R$	6	V				
Forward current		I <sub>F</sub>	60	mA				
Forward surge current	t <sub>p</sub> ≤ 10 μs	I <sub>FSM</sub>	1.5	Α				
Power dissipation		P <sub>diss</sub>	100	mW				
Junction temperature		T <sub>j</sub>	125	°C				
OUTPUT								
Collector emitter voltage		V <sub>CEO</sub>	70	V				
Emitter collector voltage		V <sub>ECO</sub>	7	V				
Collector current		I <sub>C</sub>	50	mA				
Collector peak current	$t_p/T = 0.5, t_p \le 10 \text{ ms}$	I <sub>CM</sub>	100	mA				
Power dissipation		P <sub>diss</sub>	150	mW				
Junction temperature		T <sub>j</sub>	125	°C				
COUPLER								
Isolation test voltage (RMS)	t = 1 s	V <sub>ISO</sub>	5300	$V_{RMS}$				
Isolation voltage		V <sub>IORM</sub>	890	$V_{P}$				
Total power dissipation		P <sub>tot</sub>	250	mW				
Operating ambient temperature range		T <sub>amb</sub>	- 55 to + 100	°C				
Storage temperature range		T <sub>stg</sub>	- 55 to + 150	°C				
Soldering temperature (2)	2 mm from case, t ≤ 10 s	T <sub>sld</sub>	260	°C				

#### Notes

<sup>(2)</sup> Refer to wave profile for soldering conditions for through hole devices.

<b>ELECTRICAL CHARACTERISTICS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)								
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT		
INPUT								
Forward voltage	$I_F = \pm 50 \text{ mA}$	V <sub>F</sub>		1.25	1.6	V		
Junction capacitance	V <sub>R</sub> = 0 V, f = 1 MHz	C <sub>j</sub>		50		pF		
OUTPUT								
Collector emitter voltage	I <sub>C</sub> = 1 mA	V <sub>CEO</sub>	70			V		
Emitter collector voltage	I <sub>E</sub> = 100 μA	V <sub>ECO</sub>	7			V		
Collector emitter cut-off current	$V_{CE} = 20 \text{ V}, I_F = 0, E = 0$	I <sub>CEO</sub>		10	100	nA		
COUPLER								
Collector emitter saturation voltage	$I_F = 10 \text{ mA}, I_C = 1 \text{ mA}$	V <sub>CEsat</sub>			0.3	V		
Cut-off frequency	$V_{CE}$ = 5 V, $I_F$ = 10 mA, $R_L$ = 100 $\Omega$	f <sub>c</sub>		110		kHz		
Coupling capacitance	f = 1 MHz	C <sub>k</sub>		0.3		pF		

#### Note

Minimum and maximum values were tested requierements. Typical values are characteristics of the device and are the result of engineering
evaluations. Typical values are for information only and are not part of the testing requirements.

CURRENT TRANSFER RATIO								
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT		
I <sub>C</sub> /I <sub>F</sub>	$V_{CE} = 5 \text{ V}, I_F = 5 \text{ mA}$	CTR	50		600	%		

<sup>(1)</sup> Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.



# Optocoupler, Phototransistor Output, Vishay Semiconductors (Dual, Quad Channel)

MAXIMUM SAFETY RATINGS									
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT			
INPUT									
Forward current		I <sub>F</sub>			275	mA			
OUTPUT									
Power dissipation		P <sub>diss</sub>			400	mW			
COUPLER									
Rated impulse voltage		V <sub>IOTM</sub>			10	kV			
Safety temperature		T <sub>si</sub>			175	°C			

#### Note

According to DIN EN 60747-5-5 (see figure 2). This optocoupler is suitable for safe electrical isolation only within the safety ratings.
 Compliance with the safety ratings shall be ensured by means of suitable protective circuits.

INSULATION RATED PARAMETERS								
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Partial discharge test voltage - routine test	100 %, t <sub>test</sub> = 1 s	$V_{pd}$	1.669			kV		
Partial discharge test voltage -	$t_{Tr} = 60 \text{ s}, t_{test} = 10 \text{ s},$	$V_{IOTM}$	10			kV		
lot test (sample test)	(see figure 2)	$V_{pd}$	V <sub>pd</sub> 1.669  OTM 10  V <sub>pd</sub> 1.424  R <sub>IO</sub> 10 <sup>12</sup>		kV			
	V <sub>IO</sub> = 500 V	R <sub>IO</sub>	10 <sup>12</sup>			Ω		
Insulation resistance	V <sub>IO</sub> = 500 V, T <sub>amb</sub> = 100 °C	R <sub>IO</sub>	10 <sup>11</sup>			Ω		
modation resistance	V <sub>IO</sub> = 500 V, T <sub>amb</sub> = 150 °C (construction test only)	R <sub>IO</sub>	10 <sup>9</sup>			Ω		

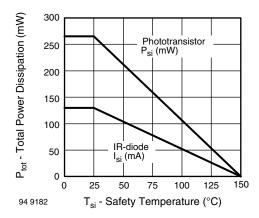


Fig. 1 - Derating Diagram

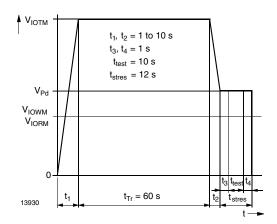


Fig. 2 - Test Pulse Diagram for Sample Test According to DIN EN 60747-5-5/DIN EN 60747-; IEC60747



## Vishay Semiconductors Optocoupler, Phototransistor Output, (Dual, Quad Channel)

SWITCHING CHARACTERISTICS								
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Delay time	$V_S = 5 \text{ V}, \ I_C = 2 \text{ mA}, \ R_L = 100 \ \Omega,$ (see figure 3)	t <sub>d</sub>		3		μs		
Rise time	$V_S = 5 \text{ V}, \ I_C = 2 \text{ mA}, \ R_L = 100 \ \Omega,$ (see figure 3)	t <sub>r</sub>		3		μs		
Turn-on time	$V_S = 5 \text{ V}, \ I_C = 2 \text{ mA}, \ R_L = 100 \ \Omega,$ (see figure 3)	t <sub>on</sub>		6		μs		
Storage time	$V_S = 5 \text{ V}, \ I_C = 2 \text{ mA}, \ R_L = 100 \ \Omega,$ (see figure 3)	t <sub>s</sub>		0.3		μs		
Fall time	$V_S = 5 \text{ V}, \ I_C = 2 \text{ mA}, \ R_L = 100 \ \Omega,$ (see figure 3)	t <sub>f</sub>		4.7		μs		
Turn-off time	$V_S = 5 \text{ V}, \ I_C = 2 \text{ mA}, \ R_L = 100 \ \Omega,$ (see figure 3)	t <sub>off</sub>		5		μs		
Turn-on time	$V_S = 5 \text{ V}, I_F = 10 \text{ mA}, R_L = 1 \text{ k}\Omega,$ (see figure 4)	t <sub>on</sub>		9		μs		
Turn-off time	$V_S = 5 \text{ V}, I_F = 10 \text{ mA}, R_L = 1 \text{ k}\Omega,$ (see figure 4)	t <sub>off</sub>		10		μs		

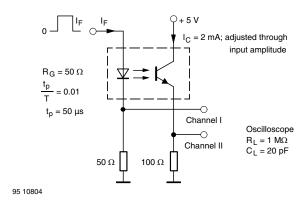


Fig. 3 - Test Circuit, Non-Saturated Operation

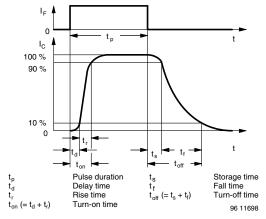


Fig. 5 - Switching Times

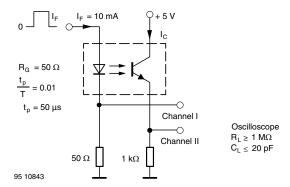


Fig. 4 - Test Circuit, Saturated Operation



## Optocoupler, Phototransistor Output, Vishay Semiconductors (Dual, Quad Channel)

### **TYPICAL CHARACTERISTICS** (T<sub>amb</sub> = 25 °C, unless otherwise specified)

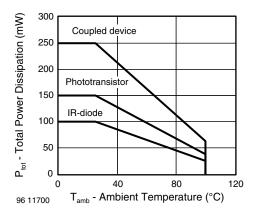


Fig. 6 - Total Power Dissipation vs. Ambient Temperature

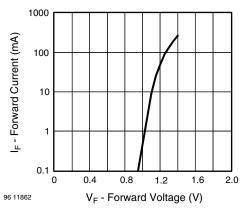


Fig. 7 - Forward Current vs. Forward Voltage

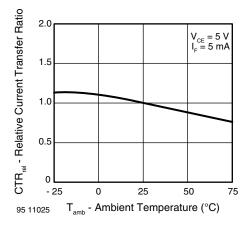


Fig. 8 - Relative Current Transfer Ratio vs. Ambient Temperature

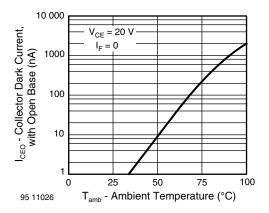


Fig. 9 - Collector Dark Current vs. Ambient Temperature

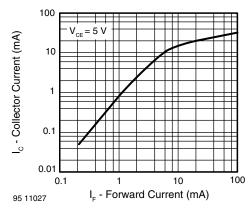


Fig. 10 - Collector Current vs. Forward Current

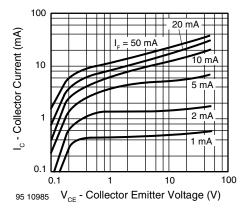


Fig. 11 - Collector Current vs. Collector Emitter Voltage

## Vishay Semiconductors Optocoupler, Phototransistor Output, (Dual, Quad Channel)



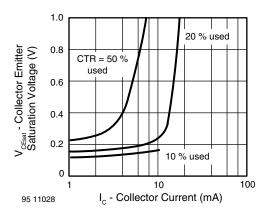


Fig. 12 - Collector Emitter Saturation Voltage vs. Collector Current

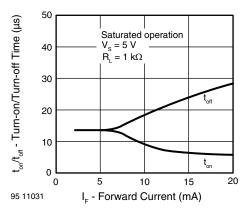


Fig. 15 - Turn-on/off Time vs. Forward Current

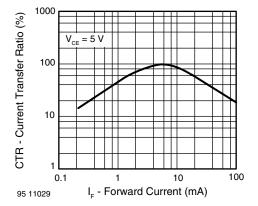


Fig. 13 - Current Transfer Ratio vs. Forward Current

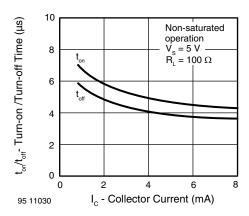
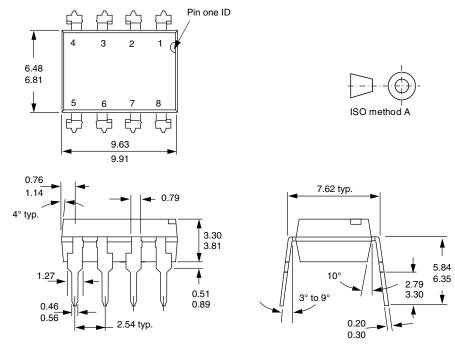


Fig. 14 - Turn-on/off Time vs. Collector Current

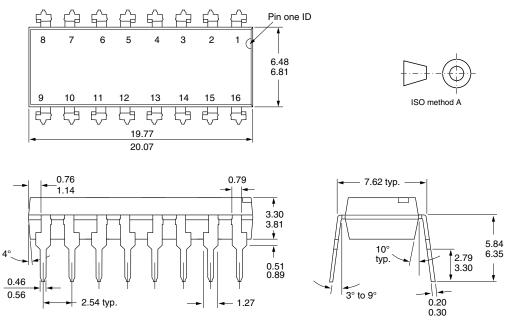


# Optocoupler, Phototransistor Output, Vishay Semiconductors (Dual, Quad Channel)

### **PACKAGE DIMENSIONS** in millimeters



i178006



i178007

### **PACKAGE MARKING**





### **Legal Disclaimer Notice**

Vishay

### **Disclaimer**

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

### **Material Category Policy**

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.

Revision: 02-Oct-12 Document Number: 91000

## **Mouser Electronics**

**Authorized Distributor** 

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Vishay:

TCET4100 TCET2100